

Session Title: [FF4] Emerging Devices and Materials for RF Systems

Session Date: December 5 (Fri.), 2025

Session Time: 15:20-17:00
Session Room: Room F (302)

[FF4-1] [Invited] 15:20-15:40

Ultra-Low Power Wideband Cryogenic CMOS Noise-Canceling LNAs for Quantum Computing

Mahesh Kumar Chaubey (National Tsing Hua University, Taiwan); Yin-Cheng Chang (Taiwan Semiconductor Research Institute, National Institutes of Applied Research, Taiwan); Po-Chang Wu and Hann-Huei Tsai (Taiwan Semiconductor Research Institute, NIAR, Taiwan); Shawn S. H. Hsu (National Tsing Hua University, Taiwan)

[FF4-2] 15:40-16:00

K-Band Cryogenic VCO in 90-nm CMOS Process

Afiya Maritza (National Taiwan University of Science and Technology, Taiwan)

[FF4-3] 16:00-16:20

A First-of-Its-Kind RF Demonstration: Impact of Alignment Layers on Liquid Crystal-Based Devices

Byeongju Moon and Hogyeom Kim (Seoul National University, Korea (South)); Changjae Lee (Korea Advanced Institute of Science and Technology (KAIST), Korea (South)); Jungsuek Oh (Seoul National University, Korea (South))

[FF4-4] 16:20-16:40

Screen-Printed via Integrated with 4D-Printed Multimaterial for Microwave Circuit Applications

Seyeon Park, Junghyeon Kim, Hyeonji Song, Taehwan Jang and Sungjoon Lim (Chung-Ang University, Korea (South))

[FF4-5] 16:40-17:00

Study of Thermal Insulated Transmission Line for Superconducting Quantum Computers

Maria Fuwa (Advanced Industrial Science and Technology (AIST), Japan); Tomonori Arakawa (National Institute of Advanced Industrial Science and Technology, Japan); Noriyoshi Hashimoto, Shota Norimoto and Junta Igarashi (National Institute of Advanced Industrial Science and Technology (AIST), Japan); Makoto Minohara (Advanced Industrial Science and Technology, Japan)